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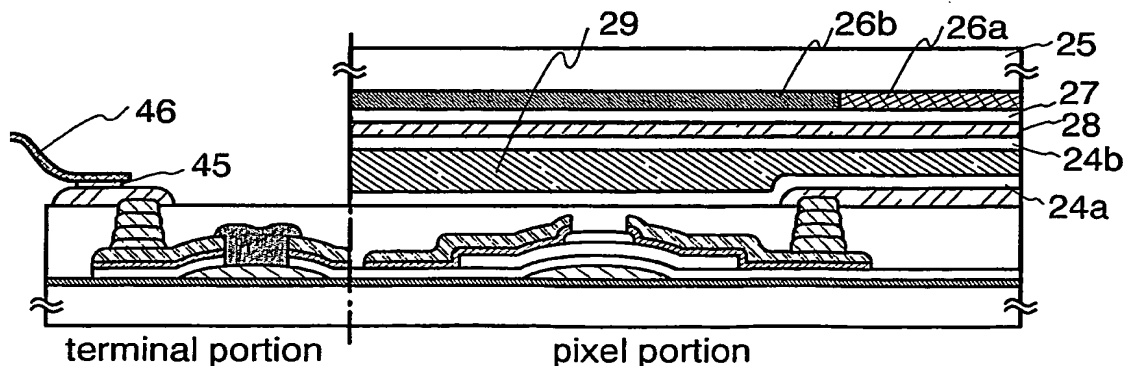
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(54) Title: LIQUID CRYSTAL DISPLAY DEVICE AND METHOD FOR MANUFACTURING THE SAME



(57) Abstract: As a substrate gets larger, time of manufacture is increased due to the repetition of film formations and etchings; waste disposal costs of etchant and the like are increased; and material efficiency is significantly reduced. A base film for improving adhesion between a substrate and a material layer formed by a droplet discharge method is formed in the invention. Further, a manufacturing method of a liquid crystal display device according to the invention includes at least one step for forming the following patterns required for manufacturing a liquid crystal display device without using a photomask: a pattern of a material layer typified by a wiring (or an electrode) pattern, an insulating layer pattern; or a mask pattern for forming another pattern.